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# BUK758R3-40E

## N-channel TrenchMOS standard level FET

11 September 2012

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in a SOT78 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

### 1.3 Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 1</a>	[1]	-	-	75	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>		-	-	96	W
<b>Static characteristics</b>							
R <sub>DS(on)</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>		-	5.8	7.4	mΩ
<b>Dynamic characteristics</b>							
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; V <sub>DS</sub> = 32 V; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>		-	7.4	-	nC

[1] Continuous current is limited by package.



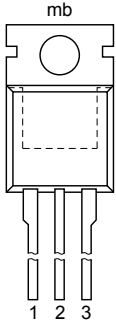
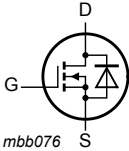
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### 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>TO-220AB (SOT78A)</p>	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

### 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK758R3-40E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

### 4. Marking

Table 4. Marking codes

Type number	Marking code
BUK758R3-40E	BUK758R3-40E

### 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ }^\circ\text{C}$ ; $T_j \leq 175\text{ }^\circ\text{C}$		-	40	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$		-	40	V
$V_{GS}$	gate-source voltage	$T_j \leq 175\text{ }^\circ\text{C}$ ; DC		-20	20	V
$I_D$	drain current	$T_{mb} = 25\text{ }^\circ\text{C}$ ; $V_{GS} = 10\text{ V}$ ; Fig. 1	[1]	-	75	A
		$T_{mb} = 100\text{ }^\circ\text{C}$ ; $V_{GS} = 10\text{ V}$ ; Fig. 1	[1]	-	59	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ }^\circ\text{C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; Fig. 4		-	331	A

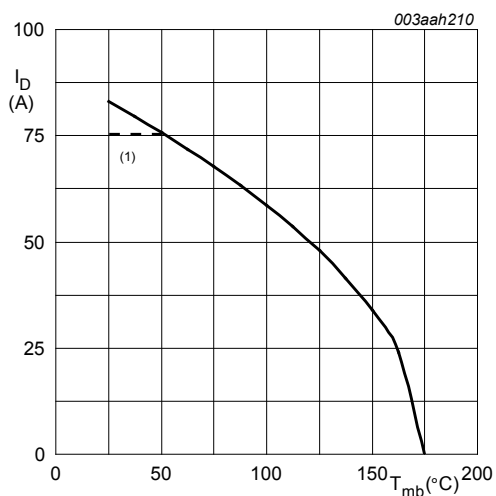
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Symbol	Parameter	Conditions		Min	Max	Unit
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>		-	96	W
$T_{stg}$	storage temperature			-55	175	°C
$T_j$	junction temperature			-55	175	°C
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25\text{ °C}$	<a href="#">[1]</a>	-	75	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$		-	331	A
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}$ ; $V_{sup} \leq 40\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; unclamped; <a href="#">Fig. 3</a>	<a href="#">[2][3]</a>	-	44	mJ

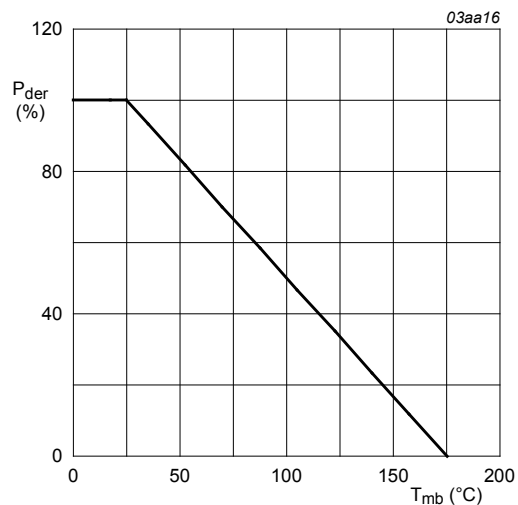
- [1] Continuous current is limited by package.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.



(1) Capped at 75A due to package

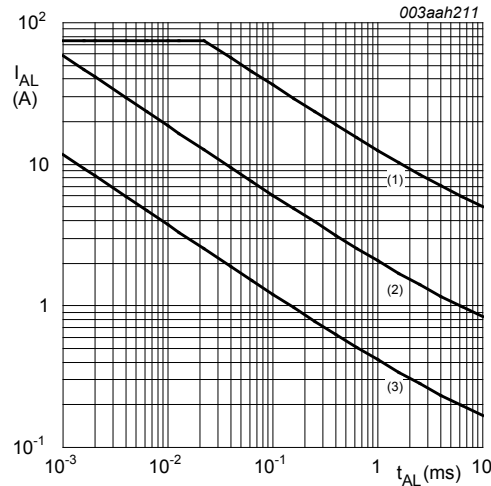
**Fig. 1. Continuous drain current as a function of mounting base temperature**

$$V_{GS} \geq 10V$$



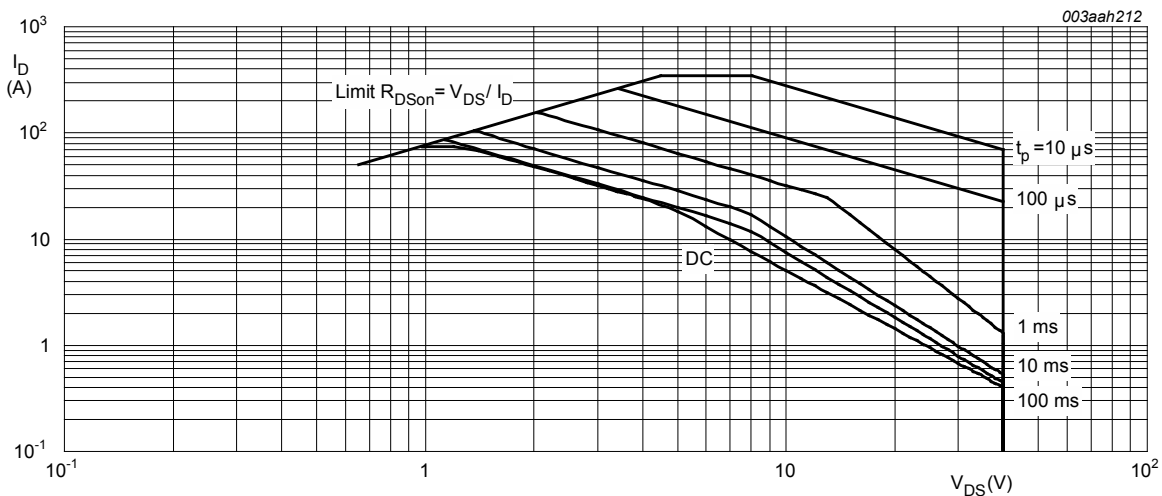
**Fig. 2. Normalized total power dissipation as a function of mounting base temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25\text{ °C})}} \times 100\%$$



**Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time**

(1)  $T_{j(jnt)} = 25^{\circ}C$ ; (2)  $T_{j(jnt)} = 150^{\circ}C$ ; (3) Repetitive Avalanche



**Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

$T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

## 6. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 5</a>	-	-	1.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

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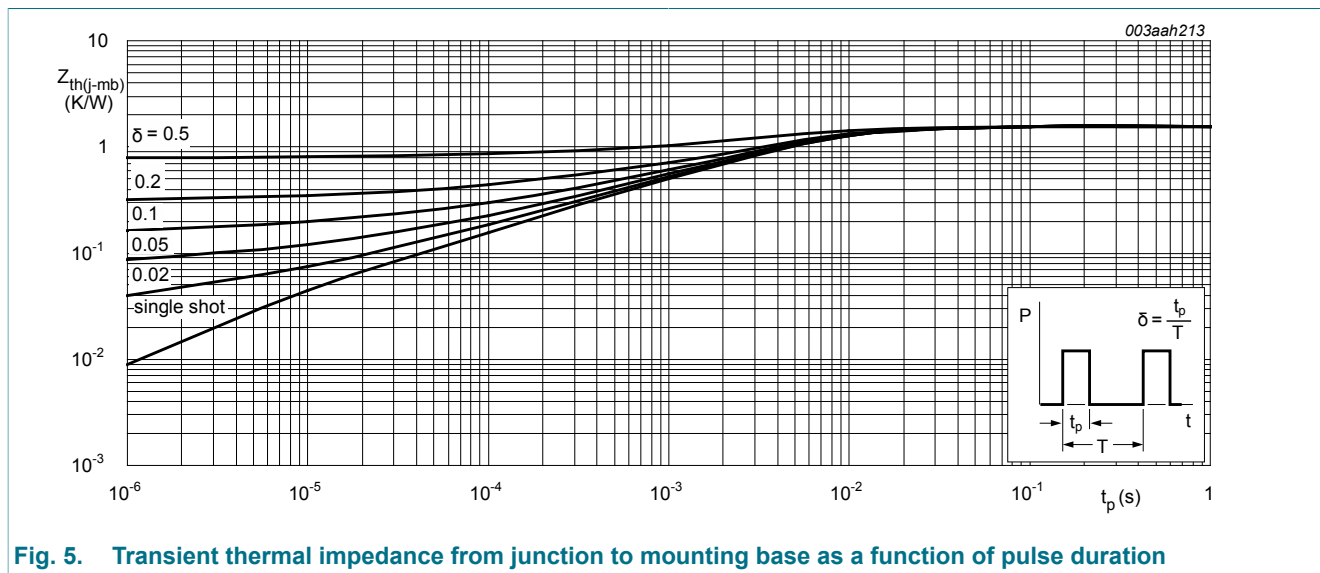


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

7. Characteristics

Table 7. Characteristics

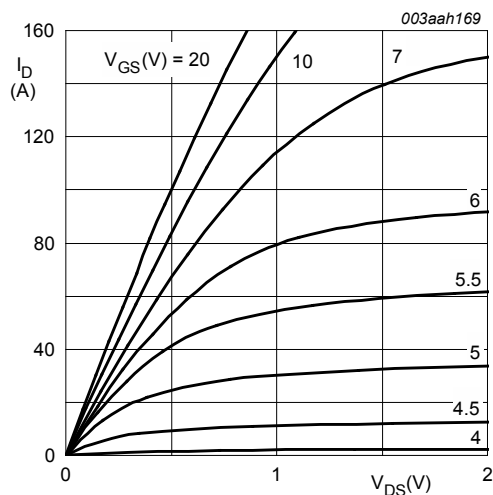
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_J = 25 \text{ }^\circ C$	40	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_J = -55 \text{ }^\circ C$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_J = 25 \text{ }^\circ C;$ <a href="#">Fig. 9; Fig. 10</a>	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_J = -55 \text{ }^\circ C;$ <a href="#">Fig. 10</a>	-	-	4.5	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_J = 175 \text{ }^\circ C;$ <a href="#">Fig. 10</a>	1	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 40 V; V_{GS} = 0 V; T_J = 25 \text{ }^\circ C$	-	0.05	1	$\mu A$
		$V_{DS} = 40 V; V_{GS} = 0 V; T_J = 175 \text{ }^\circ C$	-	-	500	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_J = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_J = 25 \text{ }^\circ C$	-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 20 A; T_J = 25 \text{ }^\circ C;$ <a href="#">Fig. 11</a>	-	5.8	7.4	m $\Omega$
		$V_{GS} = 10 V; I_D = 20 A; T_J = 175 \text{ }^\circ C;$ <a href="#">Fig. 12; Fig. 11</a>	-	-	14.1	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 20 A; V_{DS} = 32 V; V_{GS} = 10 V;$ <a href="#">Fig. 13; Fig. 14</a>	-	24	-	nC
$Q_{GS}$	gate-source charge		-	5.6	-	nC
$Q_{GD}$	gate-drain charge		-	7.4	-	nC

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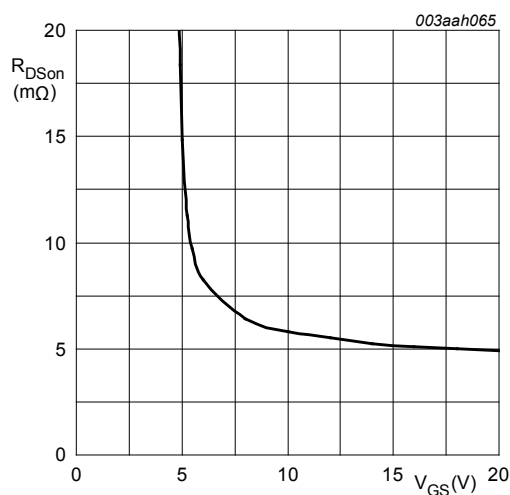
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$C_{iss}$	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 15</a>	-	1300	1730	pF
$C_{oss}$	output capacitance		-	260	312	pF
$C_{rss}$	reverse transfer capacitance		-	144	197	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30\text{ V}; R_L = 1.5\text{ }\Omega; V_{GS} = 10\text{ V}; R_{G(ext)} = 5\text{ }\Omega$	-	11	-	ns
$t_r$	rise time		-	9	-	ns
$t_{d(off)}$	turn-off delay time		-	21	-	ns
$t_f$	fall time		-	9	-	ns
$L_D$	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
$L_S$	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 20\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 16</a>	-	0.86	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20\text{ A}; dI_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}$	-	18.6	-	ns
$Q_r$	recovered charge		-	10.7	-	nC



$T_j = 25\text{ }^\circ\text{C}; t_p = 300\text{ }\mu\text{s}$

**Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values**



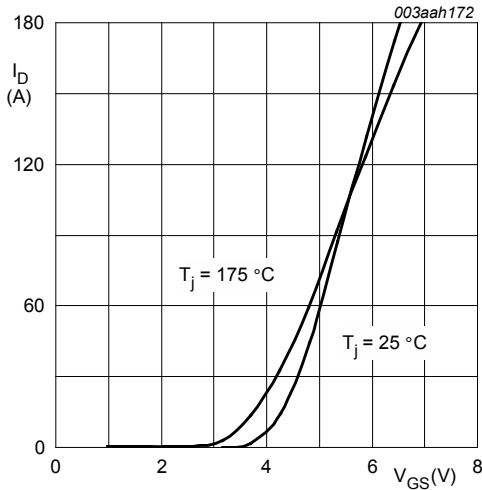
**Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values**

$T_j = 25\text{ }^\circ\text{C}; I_D = 20\text{ A}$

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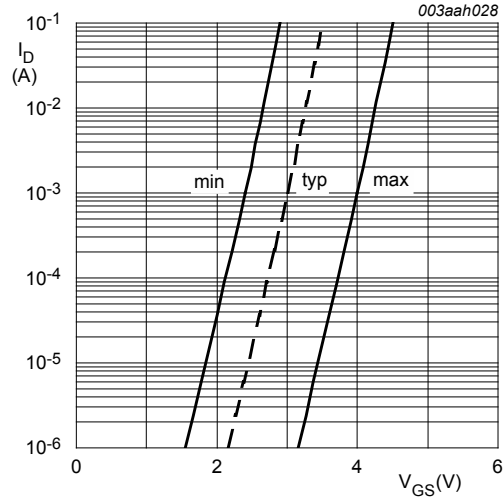
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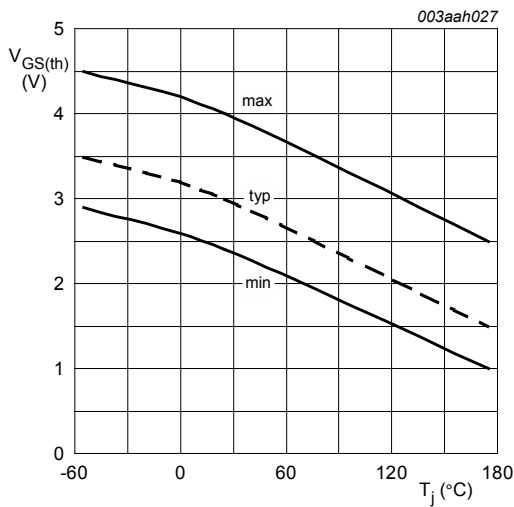
**Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values**

$V_{DS} = 10V$



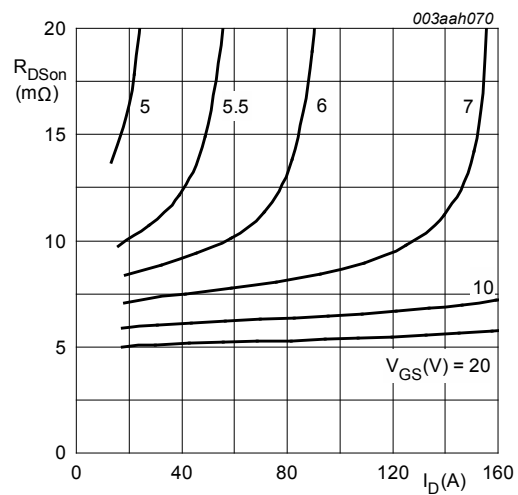
**Fig. 9. Sub-threshold drain current as a function of gate-source voltage**

$T_j = 25 °C; V_{DS} = 5V$



**Fig. 10. Gate-source threshold voltage as a function of junction temperature**

$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$



**Fig. 11. Drain-source on-state resistance as a function of drain current; typical values**

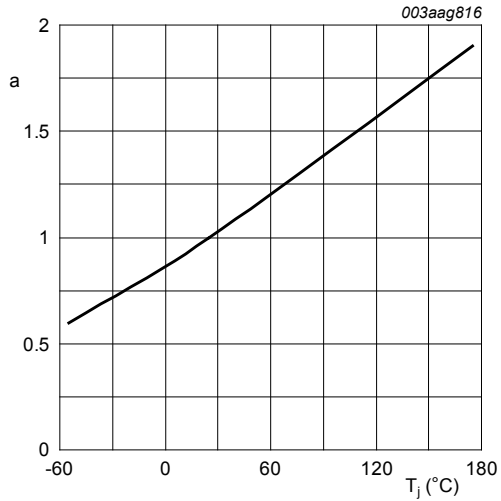
$T_j = 25 °C; t_p = 300 \mu s$



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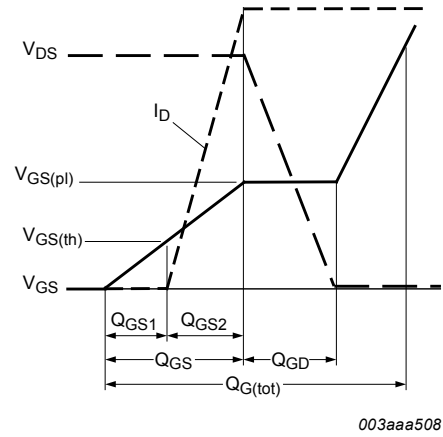
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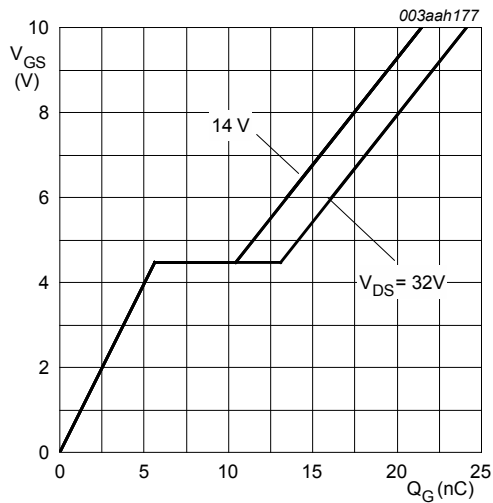


**Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature**

$$a = \frac{R_{DS(on)}}{R_{DS(on)(25^\circ C)}}$$

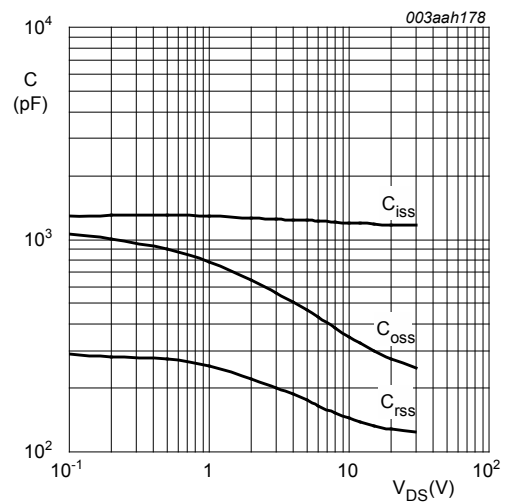


**Fig. 13. Gate charge waveform definitions**



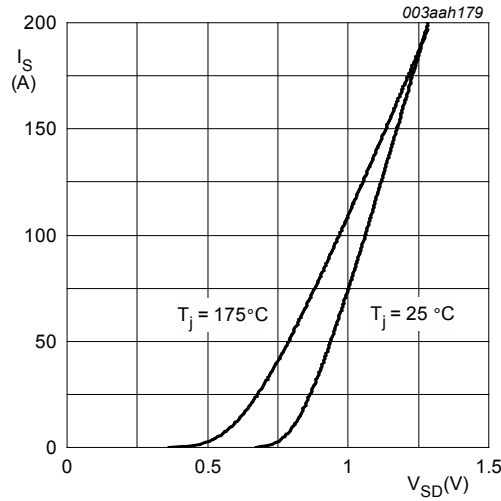
**Fig. 14. Transient thermal impedance from junction to mounting base as a function of pulse duration**

$$T_j = 25^\circ C; I_D = 15A$$



**Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

$$V_{GS} = 0V; f = 1MHz$$



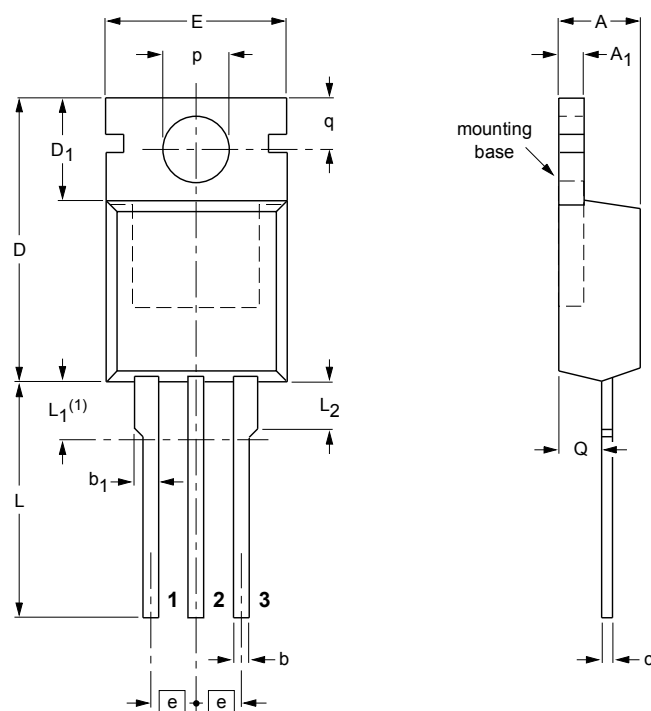
**Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values**

$$V_{GS} = 0V$$

**8. Package outline**

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78A



**DIMENSIONS** (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	c	D	D <sub>1</sub>	E	e	L	L <sub>1</sub> <sup>(1)</sup>	L <sub>2</sub> max.	p	q	Q
mm	4.5 4.1	1.39 1.27	0.9 0.6	1.3 1.0	0.7 0.4	15.8 15.2	6.4 5.9	10.3 9.7	2.54	15.0 13.5	3.30 2.79	3.0	3.8 3.6	3.0 2.7	2.6 2.2

**Note**

1. Terminals in this zone are not tinned.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78A		3-lead TO-220AB	SC-46			03-01-22- 05-03-14

**Fig. 17. Package outline TO-220AB (SOT78A)**

## 9. Legal information

### 9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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